TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM6N05FU

High Speed Switching Applications

- Small package
- Low on resistance :  $R_{on} = 0.8 \Omega (max) (@V_{GS} = 4 V)$

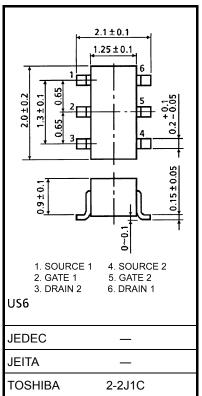
:  $R_{on} = 1.2 \Omega \text{ (max)} (@V_{GS} = 2.5 \text{ V})$ 

• Low gate threshold voltage

### Absolute Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V <sub>DS</sub>	20	V	
Gate-Source voltage		V <sub>GSS</sub>	±12	V	
Drain current	DC	I <sub>D</sub>	400	mA	
	Pulse	I <sub>DP</sub>	800		
Drain power dissipation (Ta = $25^{\circ}$ C)		P <sub>D</sub> (Note 1)	300	mW	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.



Weight: 6.8 mg (typ.)

operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating, mounted on FR4 board (25.4 mm  $\times$  25.4 mm  $\times$  1.6 t, Cu Pad: 0.32 mm  $^2 \times$  6)

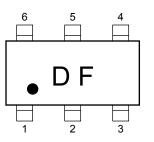
# **Handling Precaution**

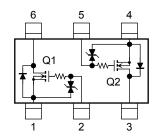
When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Unit: mm

# **TOSHIBA**

### Marking





Equivalent Circuit (top view)

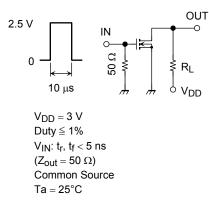
## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}=\pm 12~V,~V_{DS}=0$	_	_	±1	μA
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	20	_	_	V
Drain cut-off current		I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0$	_	_	1	μA
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.6	_	1.1	V
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 200 \text{ mA} \qquad (\text{Note2})$	350	_	_	mS
Drain-Source ON resistance		R <sub>DS (ON)</sub>	$I_D = 200 \text{ mA}, V_{GS} = 4 \text{ V} \qquad (\text{Note2})$	_	0.6	0.8	Ω
			$I_D = 200 \text{ mA}, V_{GS} = 2.5 \text{ V}$ (Note2)		0.85	1.2	
Input capacitance		C <sub>iss</sub>			22		pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 3 V$ , $V_{GS} = 0$ , f = 1 MHz		9		pF
Output capacitance		C <sub>oss</sub>			21		pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 V, I_D = 100 mA,$		60		ns
	Turn-off time	t <sub>off</sub>	V <sub>GS</sub> = 0~2.5 V	_	70	—	

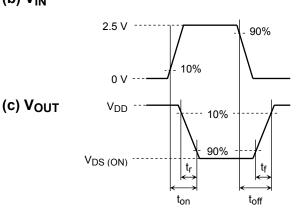
Note2: Pulse test

# **Switching Time Test Circuit**

#### (a) Test circuit



(b) V<sub>IN</sub>

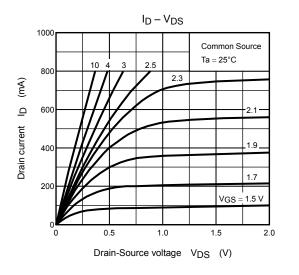


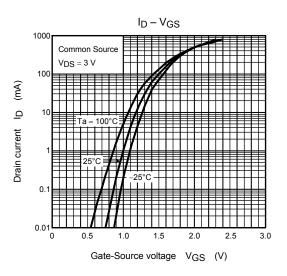
#### Precaution

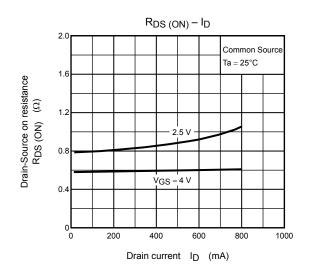
 $V_{th}$  can be expressed as voltage between gate and source when low operating current value is  $I_D = 100~\mu A$  for this product. For normal switching operation,  $V_{GS}$  (\_on) requires higher voltage than  $V_{th}$  and  $V_{GS}$  (\_off) requires lower voltage than  $V_{th}$ . (Relationship can be established as follows:  $V_{GS}$  (\_off)  $< V_{th} < V_{GS}$  (\_on) )

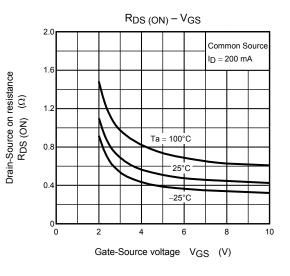
Please take this into consideration for using the device.

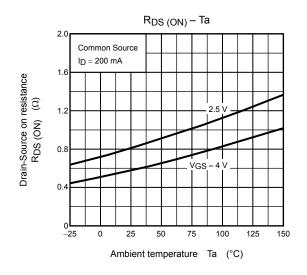
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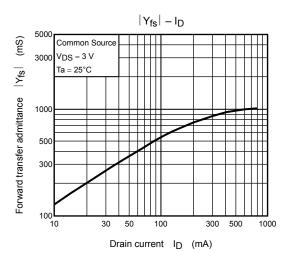






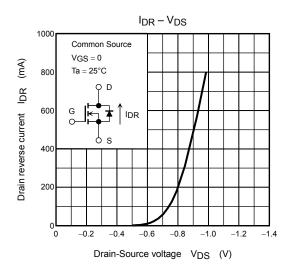


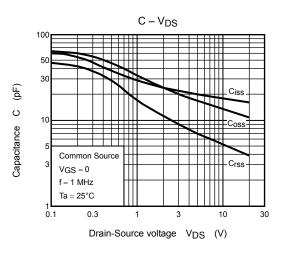


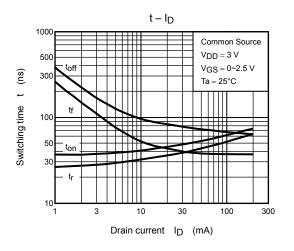


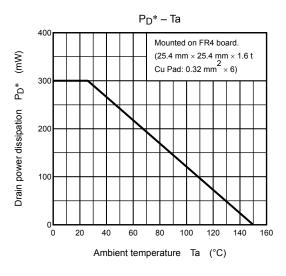
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#### (Q1, Q2 common)









\*: Total rating

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20070701-EN GENERAL

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